High Speed InGaAs Photodiodes Mounted on Wraparound Ceramic

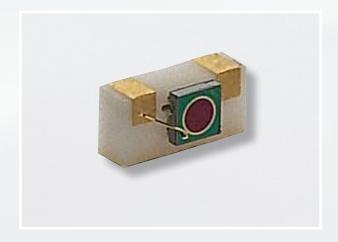
FCI-InGaAs-XXX-WCER with active area sizes of 75 μ m, 120 μ m, 300 μ m, 400 μ m and $500\mu m$ are part of a line of monitor photodiodes mounted on metallized ceramic substrates. These compact assemblies are designed for ease of integration. The chips can be epoxy or eutectic mounted onto the ceramic substrate.

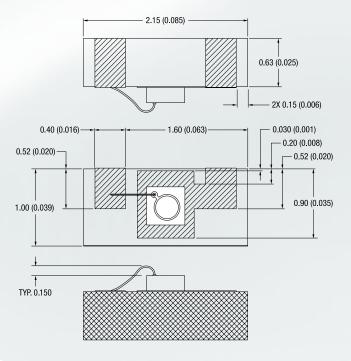
APPLICATIONS

- High Speed Optical Communications
- Gigabit Ethernet/Fibre Channel
- SONET / SDH, ATM
- Diode Laser Monitor
- Instrumentation

FEATURES

- Low Noise
- High Responsivity
- High Speed
- Spectral Range 900nm to 1700nm





Notes:

- All units in millimeters (inches).
- All devices are eutectic mounted with tolerance of ±50µm.

Absolute Maximum Ratings											
PARAMETERS	SYMBOL	MIN	MAX	UNITS							
Storage Temperature	T _{stg}	-40	+85	°C							
Operating Temperature	T _{op}	0	+70	°C							
Soldering Temperature	T _{sld}		+260	°C							

<u>`</u>													$T_A = 2$					
PARAMETERS SYMBO	SYMBOL	CONDITIONS	FCI-InGaAs-75WCER									FCI-InGaAs-400WCER						IINTTS
Active Area	AA		MIN	TYP 75	MAX	MIN	TYP 120	MAX	MIN	TYP 300	MAX	MIN	TYP 400	MAX	MIN	TYP 500	MAX	μm
Diameter $Responsivity$ R_{λ}	¥	λ=1310nm	0.80	0.90		0.80	0.90		0.80	0.90		0.80	0.90		0.80	0.90		A/W
	R _λ	λ=1550nm	0.90	0.95		0.90	0.95		0.90	0.95		0.90	0.95		0.90	0.95		
Capacitance	C _j	V _R = 5.0V		0.65			1.0			10.0			14.0			20.0		pF
Dark Current	I _d	V _R = 5.0V		0.03	2		0.05	2		0.30	5		0.40	5		0.50	20	nA
Rise Time/ Fall Time	t _r /t _f	$V_R = 5.0V,$ $R_L = 50\Omega$ 10% to 90%			0.20			0.30			1.5			3.0			10.0	ns
Max. Reverse Voltage					20			20			15			15			15	V
Max. Reverse Current					1			2			2			2			2	mA
Max. Forward Current					5			5			8			8			8	mA
NEP				3.44E- 15			4.50E- 15			6.28E- 15			7.69E- 15			8.42E- 15		W/√Hz